

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS**

**Claims 1-13.** (Cancelled)

**Claim 14.** (Currently Amended)      A power semiconductor device with trench gates comprising:

a semiconductor substrate;

a source layer on one surface of the substrate and comprising a high concentration of a dopant of one polarity;

a single drain region on the other surface of the substrate;

a well layer beneath the source layer doped with a dopant of opposite polarity;

a plurality of trenches penetrating the source layer, said trenches substantially filled with conductive material;

a highly conductive layer on the surface of the source layer comprising a material reacted from a metal and the semiconductor substrate;

an insulating layer on the highly conductive layer and on the conductive material in the trenches;

vias formed in the insulating layer and extending to the highly conductive layer on the source layer;

conductive material filling the vias for contacting the highly conductive layer.

**Claims 15-19.** (Cancelled).

**Claim 20.** (Currently Amended)      The power semiconductor device of claim 14 wherein the trenches are filled with polysilicon and the top surface of the

polysilicon is covered with a highly conductive material reacted from a metal and the semiconductor substrate polysilicon.

**Claim 21.** (Previously Presented) The power semiconductor device of claim 14 wherein the highly conductive layer is a silicide.

**Claim 22.** (Cancelled).

**Claim 23.** (Currently Amended) The power semiconductor device of claim 20 [[22]] or 21 [[23]] wherein the silicide is reacted from platinum or titanium.

**Claim 24.** (Currently Amended) The power semiconductor device of claim 14 wherein the insulating material on the highly conductive ~~source~~ layer is BPSG, PSG, silicon dioxide or silicon nitride.

**Claim 25.** (Currently Amended) The power semiconductor device of claim 14 wherein the trenches are lined with a trench wall insulating material and the insulating material on the highly conductive ~~source~~ layer contacts the ends of the trench wall insulating layer lining the walls of the trenches.

**Claim 26.** (Currently Amended) The power semiconductor device of claim 14 wherein one or more vias terminated on the surface of the highly conductive ~~source~~ layer for making electrical contact between the highly conductive source layer and the conductive material filling the via(s).